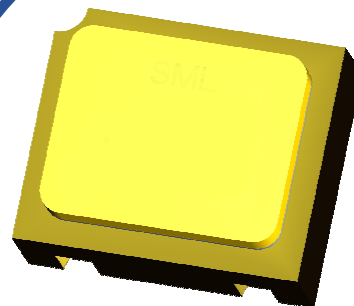


SILICON SMALL SIGNAL N-CHANNEL JFET

2N4416AC1

- Low Noise, High Gain.
- Hermetic Surface Mounted Package.
- Designed For VHF/UHF Amplifiers, Oscillators And Mixers.
- Screening Options Available.



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise stated)

V _{DS}	Drain – Source Voltage	35V
V _{GS}	Gate – Source Voltage	-35V
V _{GD}	Gate – Drain Voltage	-35V
I _G	Gate Current	10mA
P _D	Total Power Dissipation at T _A = 25°C	300mW
	Derate Above 25°C	1.7mW/°C
T _J	Junction Temperature Range	-65 to +200°C
T _{stg}	Storage Temperature Range	-65 to +200°C

THERMAL PROPERTIES (Each Device)

Symbols	Parameters	Min.	Typ.	Max.	Units
R _{θJA}	Thermal Resistance, Junction To Ambient			583	°C/W

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
$V_{(BR)GSS}$	Gate – Source Breakdown Voltage	$V_{DS} = 0$ $I_G = -1.0\mu\text{A}$	-35			V
$V_{GS(off)}$	Gate – Source Cut-off Voltage	$V_{DS} = 15\text{V}$ $I_D = 1.0\text{nA}$	-2.5		-6	
V_{GS}	Gate – Source Voltage	$V_{DS} = 15\text{V}$ $I_D = 0.5\text{mA}$	-1.0		-5.5	
$I_{DSS}^{(1)}$	Saturation Drain Current	$V_{DS} = 15\text{V}$ $V_{GS} = 0$	5		15	mA
I_{GSS}	Gate Reverse Current	$V_{DS} = 0$ $V_{GS} = -20\text{V}$			-100	pA
		$T_A = 150^\circ\text{C}$			-100	nA
I_G	Gate Operating Current	$V_{DG} = 10\text{V}$ $I_D = 1.0\text{mA}$		-20		pA
$I_{D(off)}$	Drain Cut-off Current	$V_{DS} = 10\text{V}$ $V_{GS} = -10\text{V}$		2		
$V_{GS(F)}$	Gate – Source Forward Voltage	$V_{DS} = 0$ $I_G = 1.0\text{mA}$			1.0	V
$R_{DS(on)}$	Drain – Source On Resistance	$V_{GS} = 0$ $I_D = 1.0\text{mA}$		150		Ω

DYNAMIC CHARACTERISTICS

$g_{fs}^{(1)}$	Common – Source Forward Transconductance	$V_{DS} = 15\text{V}$ $f = 1.0\text{KHz}$ $V_{GS} = 0$	4.5		7.5	mS
$g_{os}^{(1)}$	Common – Source Output Transconductance				50	μS
C_{iss}	Common – Source Input Capacitance	$V_{DS} = 15\text{V}$ $f = 1.0\text{MHz}$ $V_{GS} = 0$			4	pF
C_{oss}	Common – Source Output Capacitance				2	
C_{rss}	Common – Source Reverse Transfer Capacitance				1.2	
$b_{iss}^{(2)}$	Common – Source Input Susceptance	$V_{DS} = 15\text{V}$ $f = 100\text{MHz}$ $V_{GS} = 0$			2.5	mS
$g_{iss}^{(2)}$	Common – Source Input Conductance				0.3	
$b_{oss}^{(2)}$	Common – Source Output Susceptance				1.0	
$g_{oss}^{(2)}$	Common – Source Output Conductance				75	μS
$G_{pe}^{(2)}$	Common – Source Insertion Power Gain	$V_{DS} = 15\text{V}$ $f = 100\text{MHz}$ $I_D = 5\text{mA}$ $R_G = 1.0\text{K}\Omega$	18			dB
$NF^{(2)}$	Noise Figure				2	

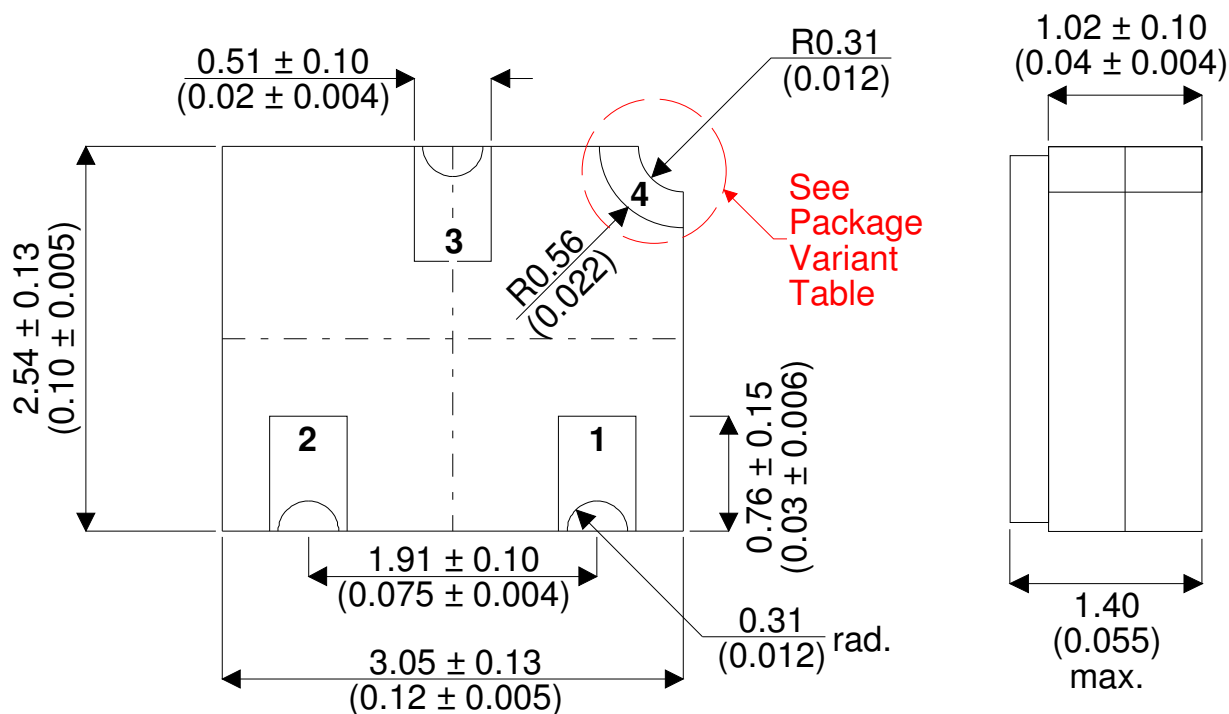
Notes

- (1) Pulse Width $\leq 300\mu\text{s}$, $\delta \leq 2\%$
(2) By design only, not a production test.

SILICON SMALL SIGNAL N-CHANNEL JFET 2N4416AC1

MECHANICAL DATA

Dimensions in mm (inches)



C1
Underside View

PACKAGE VARIANT TABLE

Variant	Pad 1	Pad 2	Pad 3	Pad 4
A	Drain	Source	Gate	No Pad (3-Pins Only)
B	Drain	Source	Gate	Lid Contact *
C	Source	Drain	Gate	No Pad (3-Pins Only)
D	Source	Drain	Gate	Lid Contact *

* The additional contact provides a connection to the lid in the application. Connecting the metal lid to a known electrical potential stops deep dielectric discharge in space applications; see the Space Weather link www.semelab.co.uk/mil/lcc1_4 on the Semelab web site. Package variant to be specified at order.

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SCREENING OPTIONS

Space Level (JQRS/ESA) and High Reliability options are available in accordance with the [High Reliability and Screening Options Handbook](#) available for download from the from the TT electronics Semelab web site.

ESA Quality Level Products are based on the testing procedures specified in the generic ESCC 5000 and in the corresponding part detail specifications.

Semelabs QR216 and QR217 processing specifications (JQRS), in conjunction with the companies ISO 9001:2000 approval present a viable alternative to the American MIL-PRF-19500 space level processing.

QR217 (Space Level Quality Conformance) is based on the quality conformance inspection requirements of MIL-PRF-19500 groups A (table V), B (table VIa), C (table VII) and also ESA / ESCC 5000 (chart F4) lot validation tests.

QR216 (Space Level Screening) is based on the screening requirements of MIL-PRF-19500 (table IV) and also ESA /ESCC 5000 (chart F3).

JQRS parts are processed to the device data sheet and screened to QR216 with conformance testing to Q217 groups A and B in accordance with MIL-STD-750 methods and procedures.

Additional conformance options are available, for example Pre-Cap Visual Inspection, Buy-Off Visit or Data Packs. These are chargeable and must be specified at the order stage (See Ordering Information). Minimum order quantities may apply.

Alternative or additional customer specific conformance or screening requirements would be considered. Contact Semelab sales with enquiries.

MARKING DETAILS

Screened parts are typically marked with specification number, serial number (or week of seal) as shown in the example below. All non screened parts are printed with three characters only eg. 22A.

Customer specific marking requirements can be arranged at time of order but is approximately limited to two lines of 7 Characters. This is to ensure text remains readable..

Example Marking:



ORDERING INFORMATION

Part number is built from part, package variant and screening level. The part number can be extended to include the additional options as shown below.

Type – See Electrical Stability Characteristics Table

Package Variant – See Mechanical Data

Screening Level – See Screening Options (ESA / JQRS)

Additional Options:

Customer Pre-Cap Visual Inspection	.CVP
Customer Buy-Off visit	.CVB
Data Pack	.DA
Solderability Samples	.SS
Scanning Electron Microscopy	.SEM
Radiography (X-ray)	.XRAY
Total Dose Radiation Test	.RAD
MIL-PRF-19500 (QR217)	
Group B charge	.GRPB
Group B destructive mechanical samples	.GBDM (12 pieces)
Group C charge	.GRPC
Group C destructive electrical samples	.GCDE (12 pieces)
Group C destructive mechanical samples	.GCDM (6 pieces)
ESA/ESCC	
Lot Validation Testing (subgroup 1) charge	.LVT1
LVT1 destructive samples (environmental)	.L1DE (15 pieces)
LVT1 destructive samples (mechanical)	.L1DM (15 pieces)
Lot Validation Testing (subgroup 2) charge	.LVT2
LVT2 endurance samples (electrical)	.L2D (15 pieces)
Lot Validation Testing (subgroup 3) charge	.LVT3
LVT3 destructive samples (mechanical)	.L3D (5 pieces)

Additional Option Notes:

- 1) All 'Additional Options' are chargeable and must be specified at order stage.
- 2) When Group B,C or LVT is required, additional electrical and mechanical destructive samples must be ordered
- 3) All destructive samples are marked the same as other production parts unless otherwise requested.

Example ordering information:

The following example is for the 2N4416AC1 part, package variant B, JQRS screening, additional Group C conformance testing and a Data pack.

Part Numbers:

2N4416AC1B-JQRS (Include quantity for flight parts)
2N4416AC1B-JQRS.GRPC (chargeable conformance option)
2N4416AC1B-JQRS.GCDE (charge for destructive parts)
2N4416AC1B-JQRS.GCDM (charge for destructive parts)
2N4416AC1B-JQRS.DA (charge for Data pack)

Customers with any specific requirements (e.g. marking, package or screening) may be supplied with a similar alternative part number (there is maximum 20 character limit to part numbers). Contact Semelab sales with all enquiries